



**For Immediate Release**

**GENUSION TO SHARE ITS B4-FLASH'S TECHNOLOGY  
BREAKTHROUGH IN NOR FLASH MEMORY ARENA**

**GENUSION Presented B4-Flash Memory Cell Miniaturization and Productization at IMW**

**Monterey, California, May 13, 2009** – GENUSION, Inc. announced its breakthrough of gate length limitation in NOR flash memory technology by GENUSION's proprietary B4-Flash (Back Bias assisted Band-to-Band tunneling-induced, Hot-Election injection-Flash) technology at the 1st IMW (International Memory Workshop) held in Monterey, California on May 13, 2009.

GENUSION presented the breakthrough of B4-Flash; it overcomes the Gate Length Limitation which NOR flash memory technology has and prohibits making memory cell size smaller. While existing NOR flash technology has gate length limitation around 110nm, B4-Flash has superior scalability. In the presentation, GENUSION demonstrated that 90nm gate length flash memory cell is possible using B4-Flash technology 64Mbit test array chip. Array functionality has been verified and other detail circuit characterizations of building blocks of flash memory chip have been done using the same test chip. These results prove GENUSION's readiness towards Productization of B4-Flash technology.

At the 2006 Symposium on VLSI Technology, GENUSION introduced its B4-Flash architecture and discussed its scalability potential. At the 2007 NVSMW conference, GENUSION presented operational test findings around B4-Flash's performance advantages. Last year at the joint workshop of NVSMW and ICMTD (International Conference on Memory Technology and Design), GENUSION presented B4-Flash's superior reliability over existing flash memory technology including interpretations of physical mechanism of such high reliability data.

"I'm honored that GENUSION and its B4-Flash have been selected to share with such an esteemed group of experts and specialists in the memory field. We appreciate the opportunity to update our progress and the major milestone of our B4-Flash technology aiming to deliver Giga bit class product samples in 2009 Q4 and volume products in 2010 Q2," noted Moriyoshi Nakashima, GENUSION's founder and President.

**About IMW**

IMW (International Memory Workshop) is organized by IEEE (The Institute of Electrical and Electronics Engineers) combining NVSMW (Nonvolatile Semiconductor Memory Workshop) and ICMTD (International Conference on Memory Technology and Design). The last year, joint conference was held and this year, it is the first workshop as IMW. This new workshop brings together experts and specialists in all aspects of memory (nonvolatile and volatile) microelectronics.

**About GENUSION, Inc.**

Founded in 2002, GENUSION is pioneering a breakthrough approach and capability in flash memory technology. Its B4-Flash (Back Bias assisted Band-to-Band tunneling-induced, Hot-Election injection-Flash) technology offers superior programming performance, excellent reliability, and reduces the cell size in half compared to conventional NOR flash memory. GENUSION's memory products are built on

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the company's own memory technologies and SiP design capabilities, in collaboration with leading semiconductor makers, assembly and test manufacturers and sales companies. Based in Amagasaki, Japan, GENUSION is a privately-held company.

For more information, interested parties can visit [http://www.genusion.co.jp/index\\_e.html](http://www.genusion.co.jp/index_e.html)